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				Application Number	10/731,517-Conf. #3730
				Filing Date	December 9, 2003
				First Named Inventor	Erik S. Jeng
				Art Unit	2815
				Examiner Name	E. Lee
Sheet	1	of	1	Attorney Docket Number	386998041US

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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EL	CA	Jeng, Erik S. et al, "Investigation of Programming Charge Distribution in Nonoverlapped Implantation nMOSFETs", IEEE Trans. Electron Devices, Vol. 53, no. 10, pp. 2517-2524, Oct. 2006).		
EL	CB	Luksy, E. et al, "Investigation of channel hot electron injection by localized charge-trapping nonvolatile memory devices," IEEE Trans. Electron Devices, vol. 51, no. 3, pp. 444-451, Mar. 2004).		
EL	CC	Makwana, Jitu J. et al, "A Nonvolatile Memory Overview". (website: http://aplawrence.com/Makwana/nonvolmem.html).		

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